

# Anode Shorted Gate Turn-Off Thyristor Types G2000HF250

## Absolute Maximum Ratings

	<b>VOLTAGE RATINGS</b>	<b>MAXIMUM LIMITS</b>	<b>UNITS</b>
$V_{DRM}$	Repetitive peak off-state voltage, (note 1)	2500	V
$V_{RSM}$	Non-repetitive peak off-state voltage, (note 1)	2500	V
$V_{DC-link}$	Maximum continuous DC-link voltage	1250	V
$V_{RRM}$	Repetitive peak reverse voltage	18	V
$V_{RSM}$	Non-repetitive peak reverse voltage	18	V

	<b>RATINGS</b>	<b>MAXIMUM LIMITS</b>	<b>UNITS</b>
$I_{TGQ}$	Peak turn-off current, (note 2)	2000	A
$L_s$	Snubber loop inductance, $I_{TM}=I_{TGQ}$ , (note 2)	200	nH
$I_{T(AV)M}$	Mean on-state current, $T_{sink}=55^{\circ}C$ (note 3)	1030	A
$I_{T(RMS)}$	Nominal RMS on-state current, $25^{\circ}C$ (note 3)	2050	A
$I_{TSM}$	Peak non-repetitive surge current $t_p=10ms$ , (Note 4)	16	kA
$I_{TSM2}$	Peak non-repetitive surge current $t_p=2ms$ , (Note 4)	28	kA
$I^2t$	$I^2t$ capacity for fusing $t_p=10ms$	$1.28 \times 10^6$	$A^2s$
$di/dt_{cr}$	Critical rate of rise of on-state current, (note 5)	500	$A/\mu s$
$P_{FGM}$	Peak forward gate power	120	W
$P_{RGM}$	Peak reverse gate power	12	kW
$I_{FGM}$	Peak forward gate current	60	A
$V_{RGM}$	Peak reverse gate voltage (note 6).	18	V
$T_{j op}$	Operating temperature range	-40 to +125	$^{\circ}C$
$T_{stg}$	Storage temperature range	-40 to +125	$^{\circ}C$

**Notes:-**

- 1)  $V_{GK}=-2Volts$ .
- 2)  $T_j=125^{\circ}C$ ,  $V_D=1250V$ ,  $V_{DM} \leq 2500V$   $di_{GQ}/dt=30A/\mu s$ ,  $I_{TGQ}=2500A$  and  $C_S=4\mu F$ .
- 3) Double-side cooled, single phase; 50Hz,  $180^{\circ}$  half-sinewave.
- 4)  $T_{j(initial)}=125^{\circ}C$ , single phase,  $180^{\circ}$  sinewave, re-applied voltage  $V_D=V_R \leq 10V$ .
- 5)  $I_T=2000A$  repetitive,  $I_{GM}=25A$ ,  $di_{GM}/dt=20A/\mu s$ . For  $di/dt > 500A/\mu s$  please consult the factory.
- 6) May exceed this value during turn-off avalanche period.

**Characteristics**

	Parameter	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V <sub>TM</sub>	Maximum peak on-state voltage	-	-	2.8	I <sub>G</sub> =5A, I <sub>T</sub> =2000A	V
I <sub>L</sub>	Latching current	-	40	-	T <sub>J</sub> =25°C	A
I <sub>H</sub>	Holding current.	-	40	-	T <sub>J</sub> =25°C	A
dv/dt <sub>cr</sub>	Critical rate of rise of off-state voltage	1000	-	-	V <sub>D</sub> =3000V, V <sub>GR</sub> =-2V	V/μs
I <sub>DRM</sub>	Peak off state current	-	-	60	Rated V <sub>DRM</sub> , V <sub>GR</sub> =-2V	mA
I <sub>RRM</sub>	Peak reverse current	-	-	20	V <sub>RR</sub> =18V	mA
I <sub>GKM</sub>	Peak negative gate leakage current	-	-	20	V <sub>GR</sub> =-18V	mA
V <sub>GT</sub>	Gate trigger voltage	-	1.0	-	T <sub>J</sub> =-40°C	V
		-	0.8	1.0	T <sub>J</sub> =25°C V <sub>D</sub> =25V, R <sub>L</sub> =25mΩ	V
		-	0.6	-	T <sub>J</sub> =125°C	V
I <sub>GT</sub>	Gate trigger current	-	8	-	T <sub>J</sub> =-40°C	A
		-	-	5	T <sub>J</sub> =25°C V <sub>D</sub> =25V, R <sub>L</sub> =25mΩ	A
		0.05	-	1	T <sub>J</sub> =125°C	A
t <sub>d</sub>	Delay time	-	0.7	2	V <sub>D</sub> =1250V, I <sub>TGQ</sub> =2000A, di <sub>T</sub> /dt=200A/μs, I <sub>GM</sub> =30A, di <sub>G</sub> /dt=20A/μs, C <sub>S</sub> =4μF, R <sub>S</sub> =5Ω	μs
t <sub>gt</sub>	Turn-on time	-	3	5		μs
E <sub>on</sub>	Turn-on energy	-	-	0.4		J
t <sub>f</sub>	Fall time	-	1.5	-	V <sub>DM</sub> =2500V, I <sub>TGQ</sub> =2000A, di <sub>GQ</sub> /dt=30A/μs, V <sub>GR</sub> =-16V, C <sub>S</sub> =4μF	μs
t <sub>s</sub>	Storage time	-	-	26		μs
t <sub>gq</sub>	Turn-off time	-	-	30		μs
I <sub>GQM</sub>	Peak turn-off gate current	-	600	-		A
Q <sub>GQ</sub>	Turn-off gate charge	-	8	-		mC
t <sub>tail</sub>	Tail time	-	8.5	-		μs
E <sub>off</sub>	Turn-off energy	-	-	2.5		J
R <sub>thJK</sub>	Thermal resistance junction to sink	-	-	22	Double side cooled	K/kW
		-	-	48	Cathode side cooled	K/kW
		-	-	42	Anode side cooled	K/kW
F	Mounting force	21	-	26	(see note 2)	kN
W <sub>t</sub>	Weight	-	0.8	-		kg

## Notes:-

- 1) Unless otherwise indicated T<sub>J</sub>=125°C.
- 2) For other clamping forces, consult factory.

**Curves**

Figure 1 - On-state characteristics of Limit device

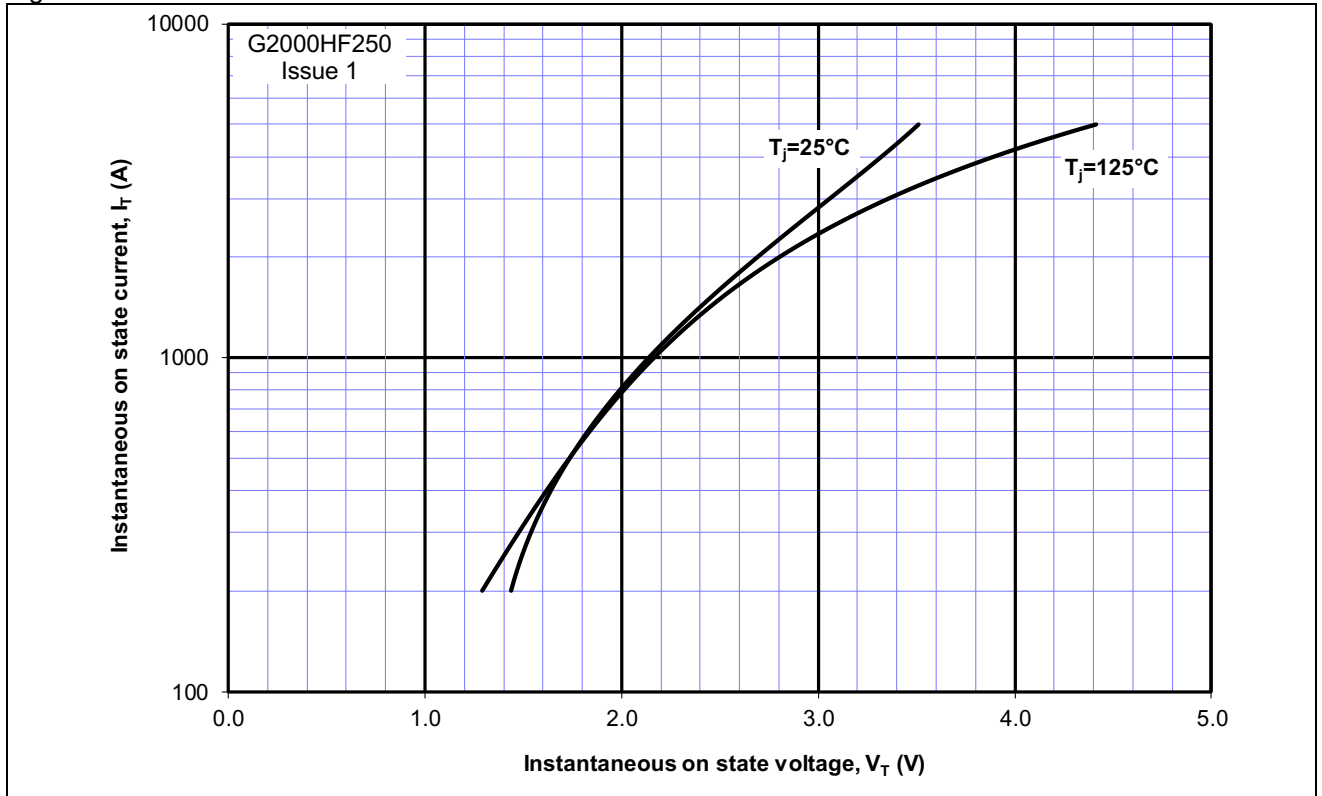
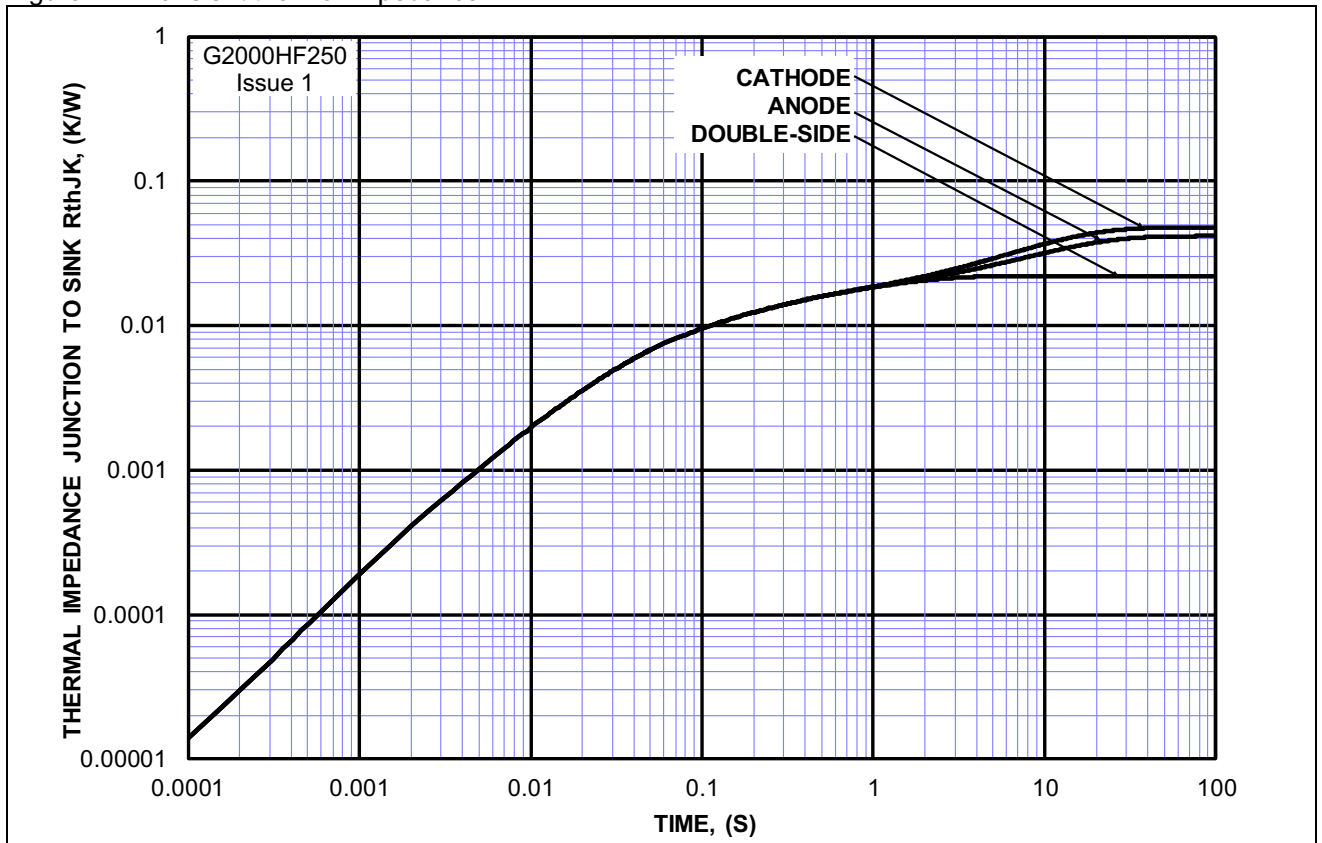
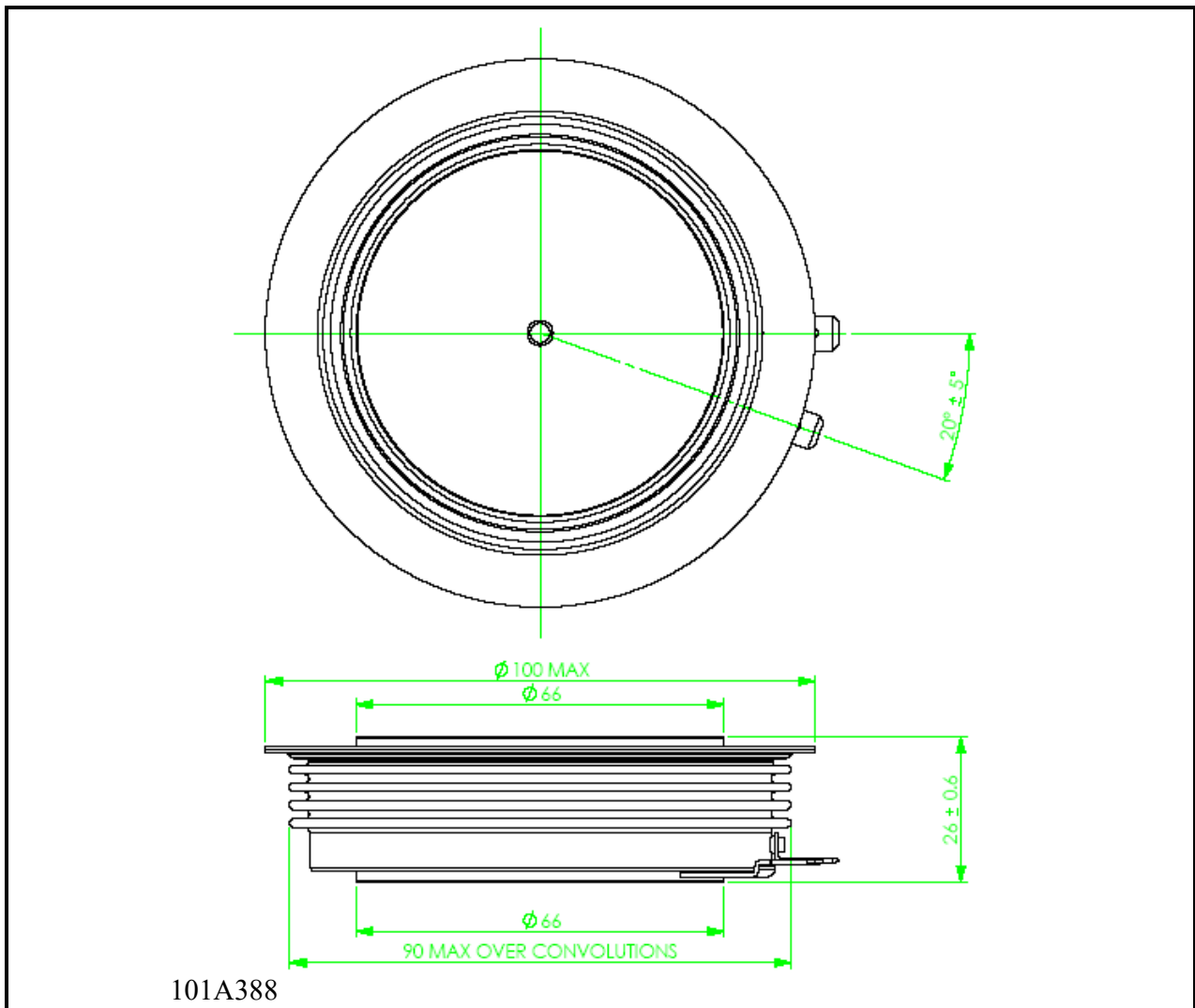


Figure 2 – Transient thermal impedance



**Outline Drawing & Ordering Information**

**ORDERING INFORMATION**

(Please quote 10-digit code as below)

<b>G2000</b>	<b>HF</b>	<b>25</b>	<b>0</b>
Fixed Type code	Outline code	Voltage code $V_{DRM}/100$	Fixed code

Order code - G2000HF250

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